

ABSTRACT

- 5 A chemical mechanical polishing slurry composition and method for using the slurry composition for polishing copper, barrier material and dielectric material that comprises first and second-step slurries. The first-step slurry has a high removal rate on copper and a low removal rate on barrier material. The second-step slurry has a high removal rate on barrier material and a low removal rate on copper and dielectric material. The first slurry comprises at least an organic polymeric abrasive.

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